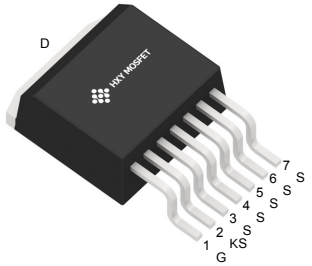
IMBG65R048M1HXTMA1

SiC Power MOSFET N-Channel Enhancement Mode

Features

- Wide bandgap SiC MOSFET technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed switching
- Low reverse recovery(Qrr)
- Halogen free, RoHs compliant



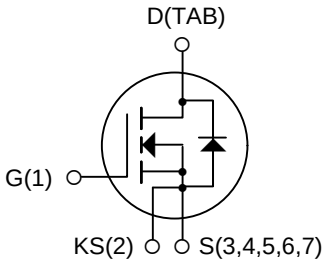
TO-263-7L

Benefits

- Reduce switching losses
- Increased system Switching Frequency
- Increased power density
- Reduction of heat sink reguirements

Applications

- Switch mode power supplies
- Renewable energy
- On Board Charger
- High Voltage DC/DC Converters



Ordering Part Number	Package	Brand
IMBG65R048M1HXTMA1	TO-263-7L	HXY MOSFET

Maximum Ratings (T_C = 25 ˚C unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit	Note
V_{DSmax}	Drain-Source Voltage	V_{GS} = 0V, I_D = 100μA	650	V	
V_{GS}	Gate-Source voltage (transient)	$t_p \leqslant$ 500ns, duty cycle ⩽1%	-8/+20	V	
V_{GSop}	Recommend Gate-Source Voltage	Static	-4/+18	V	
I_D	Continuous Drain current	V_{GS} = 18V, T_C = 25°C	70	A	Fig. 14
		V_{GS} = 18V, T_C = 100°C	49		
$I_{D,pulse}$	Pulsed Drain Current	Pulse with t_p limited by T_{jmax}	121	A	Fig.18
P_D	Power Dissipation	T_C = 25°C, Tj = 175°C	214	W	Fig.16
T_j	Operating junction temperature		-55~175	°C	
T_{stg}	Storage temperature		-55~175	°C	
	TO-247 miunting torque	M3 Screw	0.7	Nm	

Thermal Characteristics

Symbol	Parameter	Value			Unit	Note
		Min.	Typ.	Max.		
$R_{th(jc)}$	Thermal resistance from Junction to Case		0.7		K/W	Fig. 15
$R_{th(ja)}$	Thermal resistance from Junction to Ambient		40		K/W	

Electrical Characteristics (T_C = 25˚C unless other wise specified)

Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$V_{(BR)DSS}$	Drain-Source Breakdown voltage	V_{GS} = 0V, I_D = 100μA	650			V	
$V_{GS(th)}$	Gate Threshold voltage	V_{GS} = V_{DS}, I_D =12mA		2.7		V	Fig. 9
		V_{GS} = V_{DS}, I_D =12mA, T_j=175°C		1.9			
I_{GSS}	Gate-Source Leakage current	V_{GS} =18V , V_{DS} = 0V			250	nA	
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} =650V, V_{GS} = 0V, T_j = 25°C		1	50	μA	
$R_{DS(on)}$	Drain-Source On-state Resistance	V_{GS} = 15V, I_D =20A V_{GS} = 18V, I_D =20A		44 36	56	mΩ	Fig. 3, 4 , 5
		V_{GS} = 15V, I_D =20A, T_j = 175°C V_{GS} = 18V, I_D =20A, T_j = 175°C		52 47			
g_{fs}	Transconductance	V_{DS} = 18V, I_D =20A		15		S	Fig. 6
		V_{DS} = 18V, I_D =20A, T_j = 175°C		14			

Gate Charge Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
Q_{GS}	Gate to Source Charge	V_{DS} = 400V I_D =20A V_{GS} =-4V/18V		19		nC	Fig. 10
Q_{GD}	Gate to Drain Charge			21			
Q_G	Total Gate Charge			80			

AC Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 600V f=1MHz V_{AC} = 25mV		1525		pF	Fig. 13
C_{oss}	Output Capacitance			115		pF	
C_{rss}	Reverse Transfer Capacitance			3.3		pF	
$R_{G(int)}$	Internal Gate Resistance	f=1 MHz, V_{AC} = 25mV		1.4		Ω	

Reverse Diode Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
V_{SD}	Diode Forward Voltage	V_{GS} = -4V, I_{SD} = 10A		4.0		V	Fig. 7,8
		V_{GS} = -4V, I_{SD} = 10A, T_j = 175°C		3.5			
I_S	Continuous Diode Forward Current	V_{GS} = -4V, T_C = 25°C		44		A	
$I_{S,\ pulse}$	Diode pulse Current	V_{GS} = -4V, pulse width t_p limited by T_{jmax}		121		A	
t_{rr}	Reverse Recovery Time	V_{GS} = -4V, I_{SD} = 20 A, V_R = 400V dif/dt = 2700A/us		13		nS	
Q_{rr}	Reverse Recovery Charge			141		nC	
I_{rrm}	Peak Reverse Recovery Current			17		A	

Switching Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$t_{d(on)}$	Turn-On Delay Time	V_{DS} = 400V, V_{GS} = -4/+18V I_D= 20 A, $R_{G(iext)}$ = 5Ω L = 200μH		1		nS	Fig.21
t_r	Rise Time			11		nS	
$t_{d(off)}$	Turn-Off Delay Time			15		nS	
t_f	Fall Time			5		nS	
E_{on}	Turn-On Energy			19		μJ	Fig.19
E_{off}	Turn-Off Energy			25		μJ	
E_{tot}	Total switching energy			44		μJ	

Typical Performance

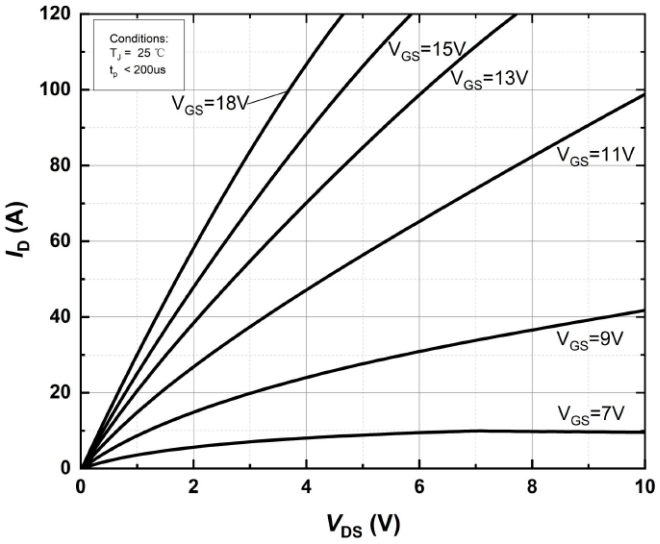


Figure 1. Output characteristics at Tj=25°C

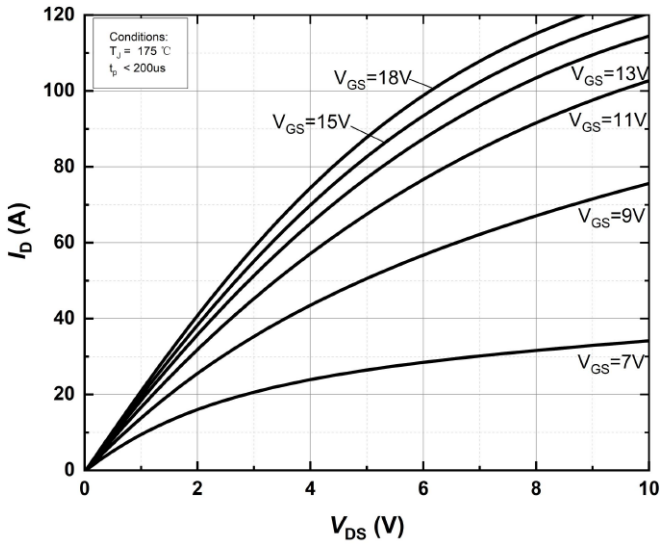


Figure 2. Output characteristics at Tj=175°C

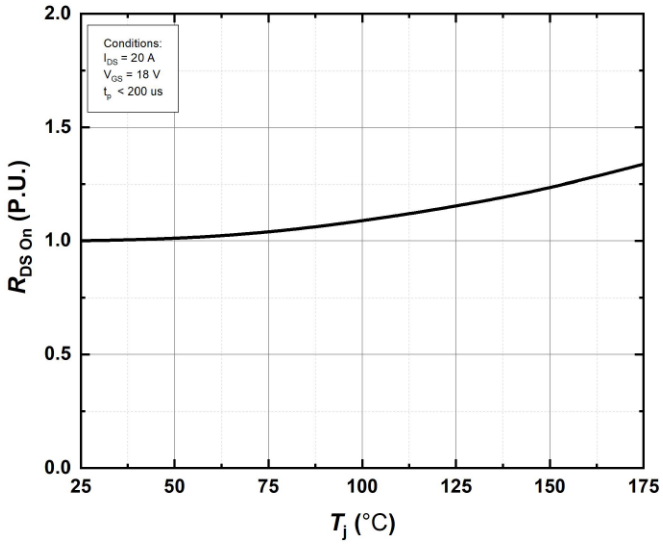


Figure 3. Normalized On-Resistance vs. Temperature

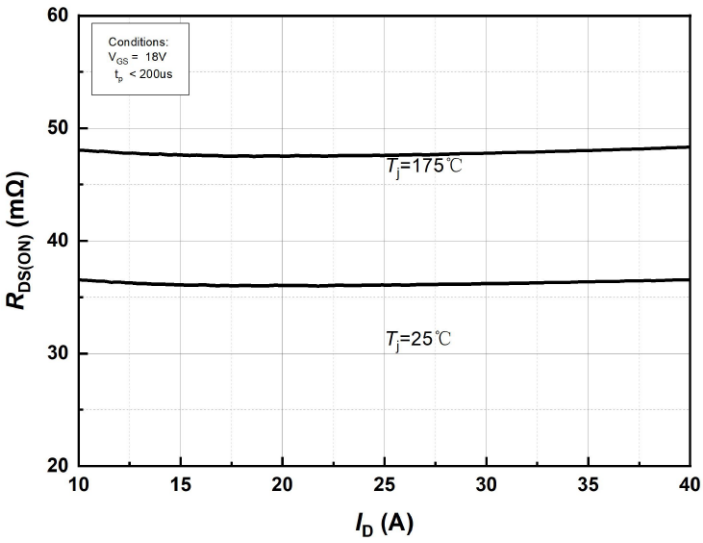


Figure 4. On-Resistance vs. Drain current for Various Temperature

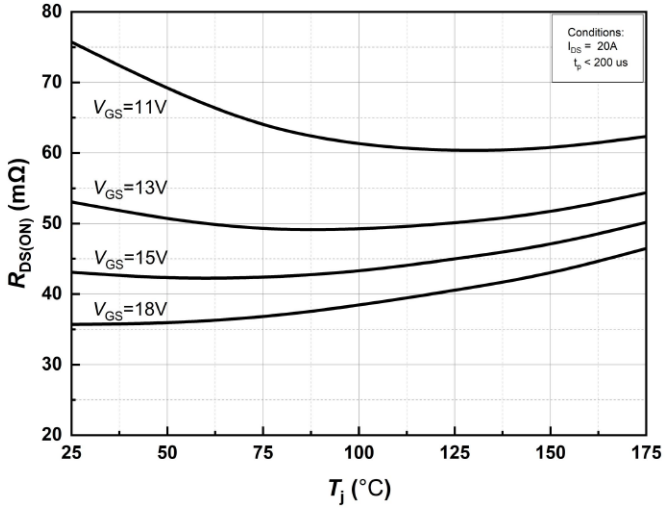


Figure 5. On-Resistance vs. Temperature for Various Gate Voltage

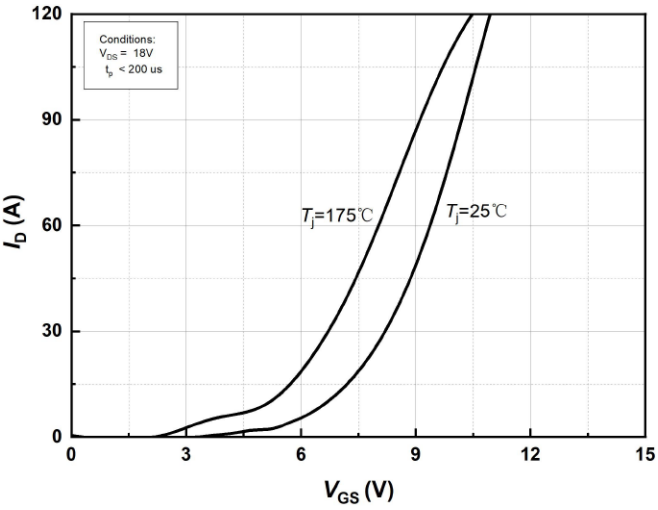


Figure 6. Transfer Characteristics for Various Junction Temperatures

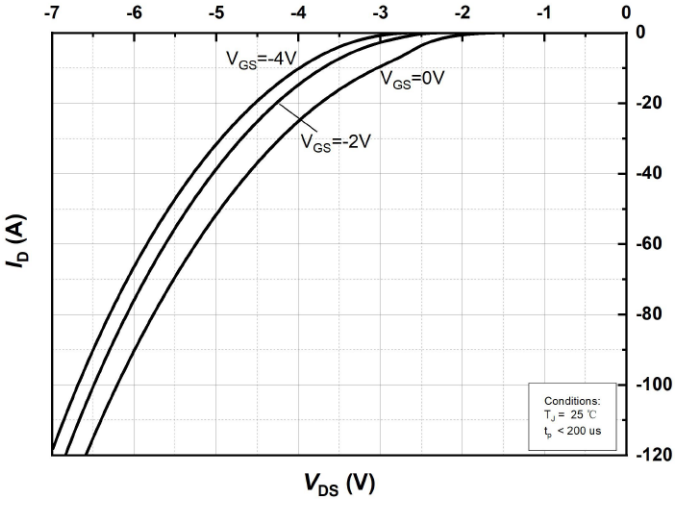


Figure 7. Body Diode Characteristics at Tj=25°C

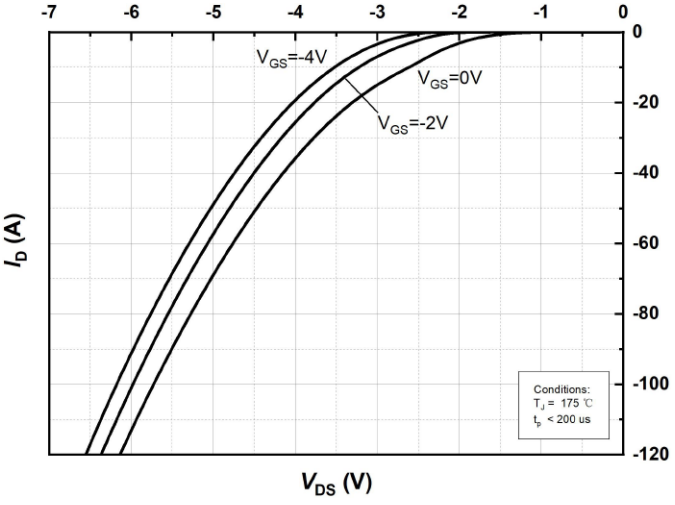


Figure 8. Body Diode Characteristics at Tj=175°C

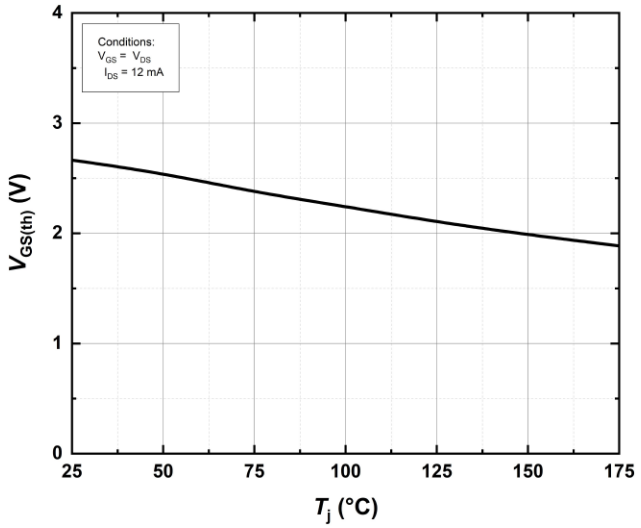


Figure 9. Threshold Voltage vs. Temperature

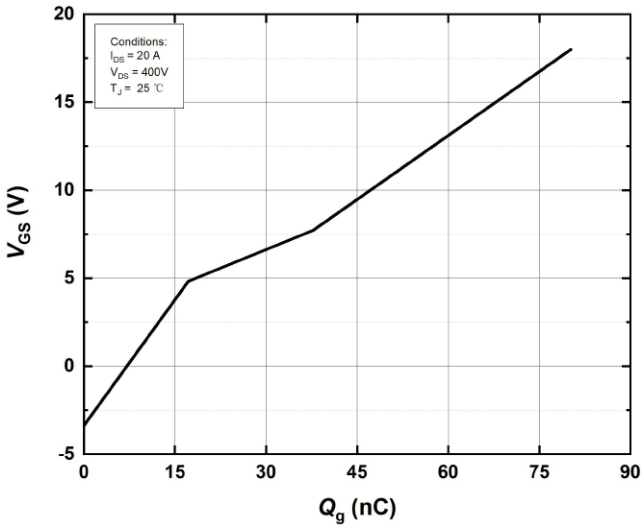


Figure 10 Gate Charge Characteristics

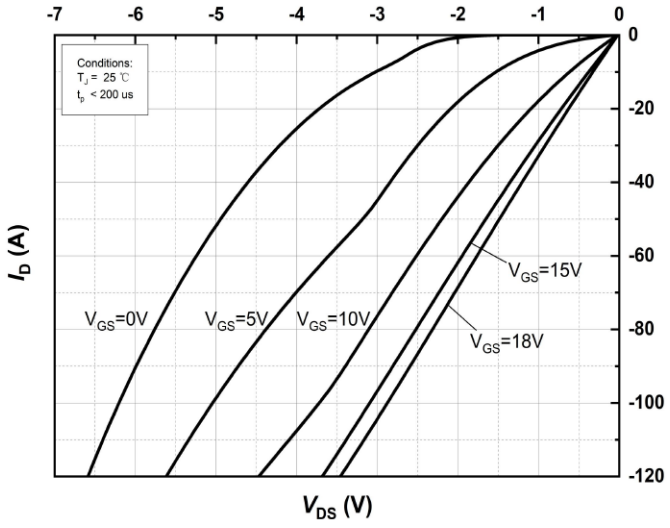


Figure 11. 3rd Quadrant Characteristic at Tj=25°C

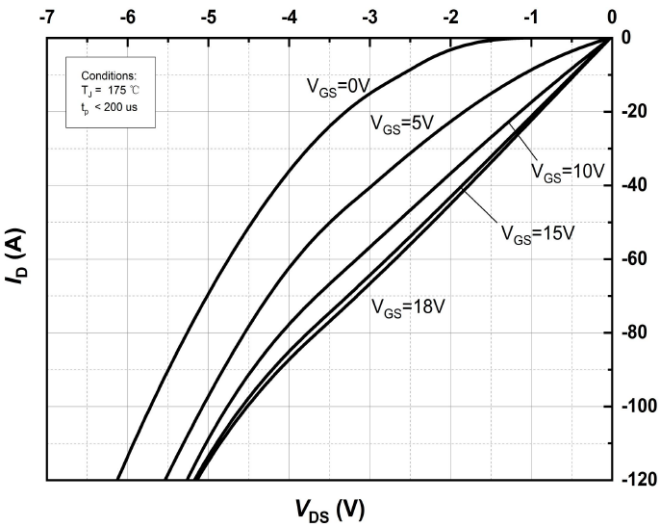


Figure 12. 3rd Quadrant Characteristic at Tj=175°C

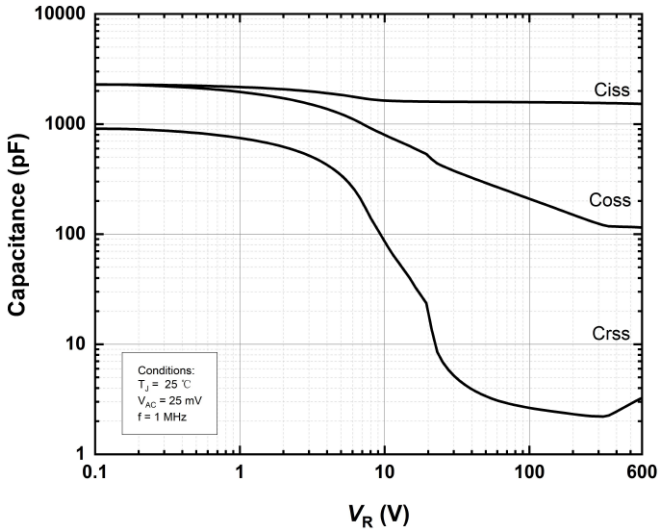


Figure 13. Capacitances vs. Drain-Source Voltage (0 – 600V)

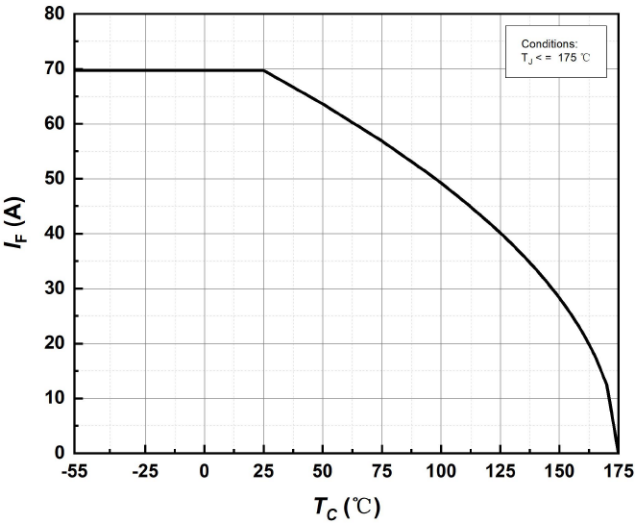


Figure 14. Continuous Drain Current Derating vs Case Temperature

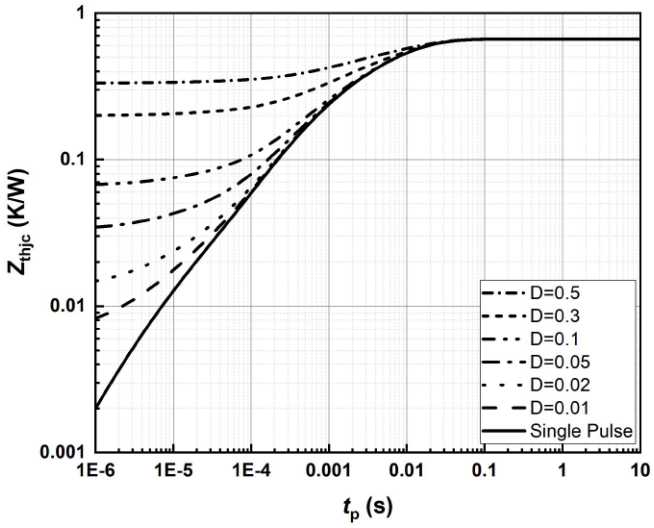


Figure 15.Transient Thermal Impedance (Junction – Case)

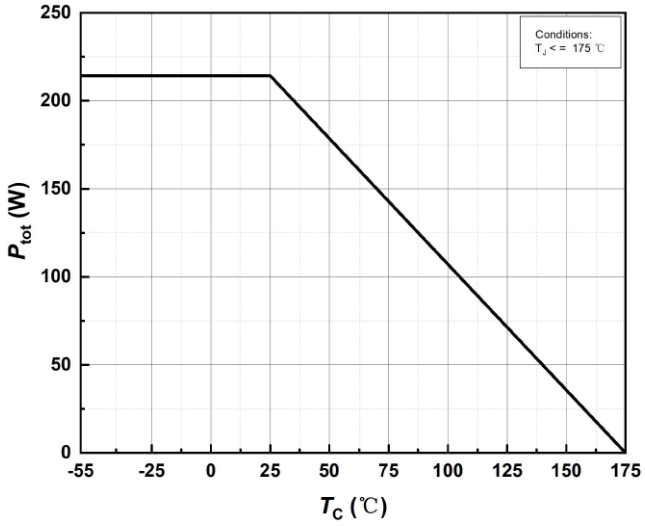


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

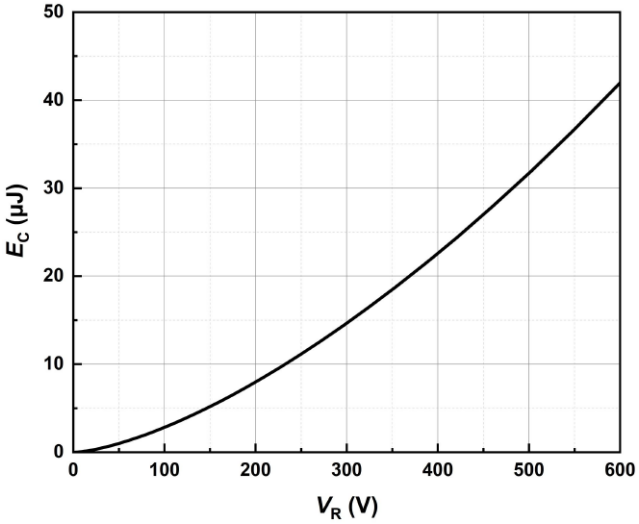


Figure 17. Output Capacitor Stored Energy

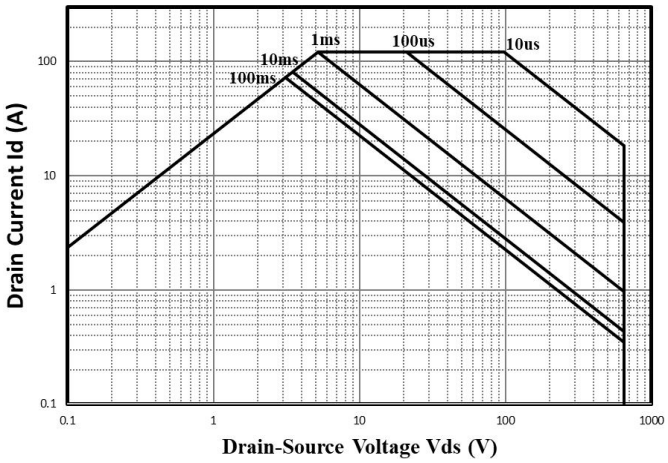


Figure 18. Safe Operating Area

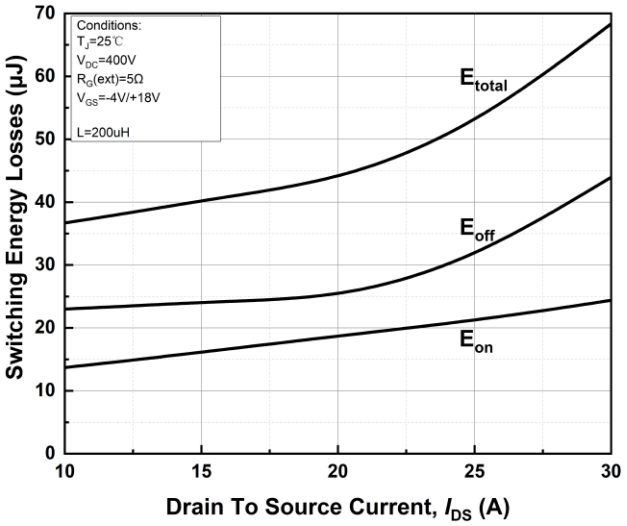


Figure 19. Clamped Inductive Switching Energy vs. Drain Current(V_{DD} = 400V)

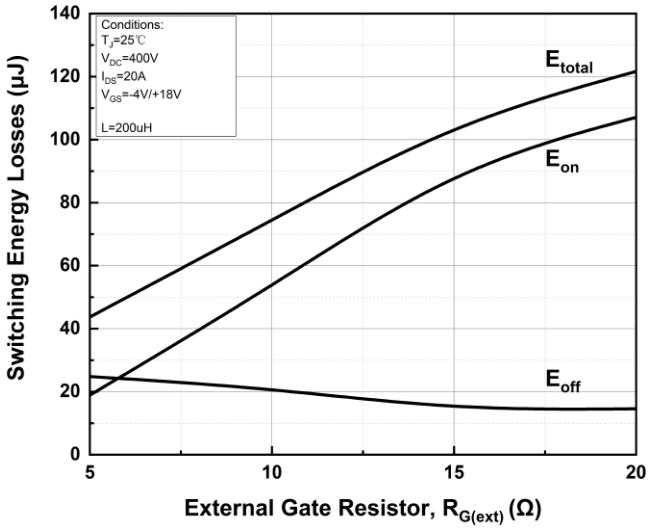


Figure 20. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

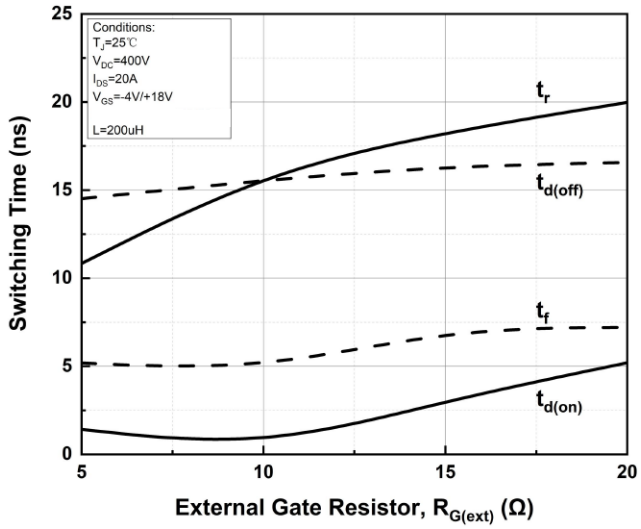
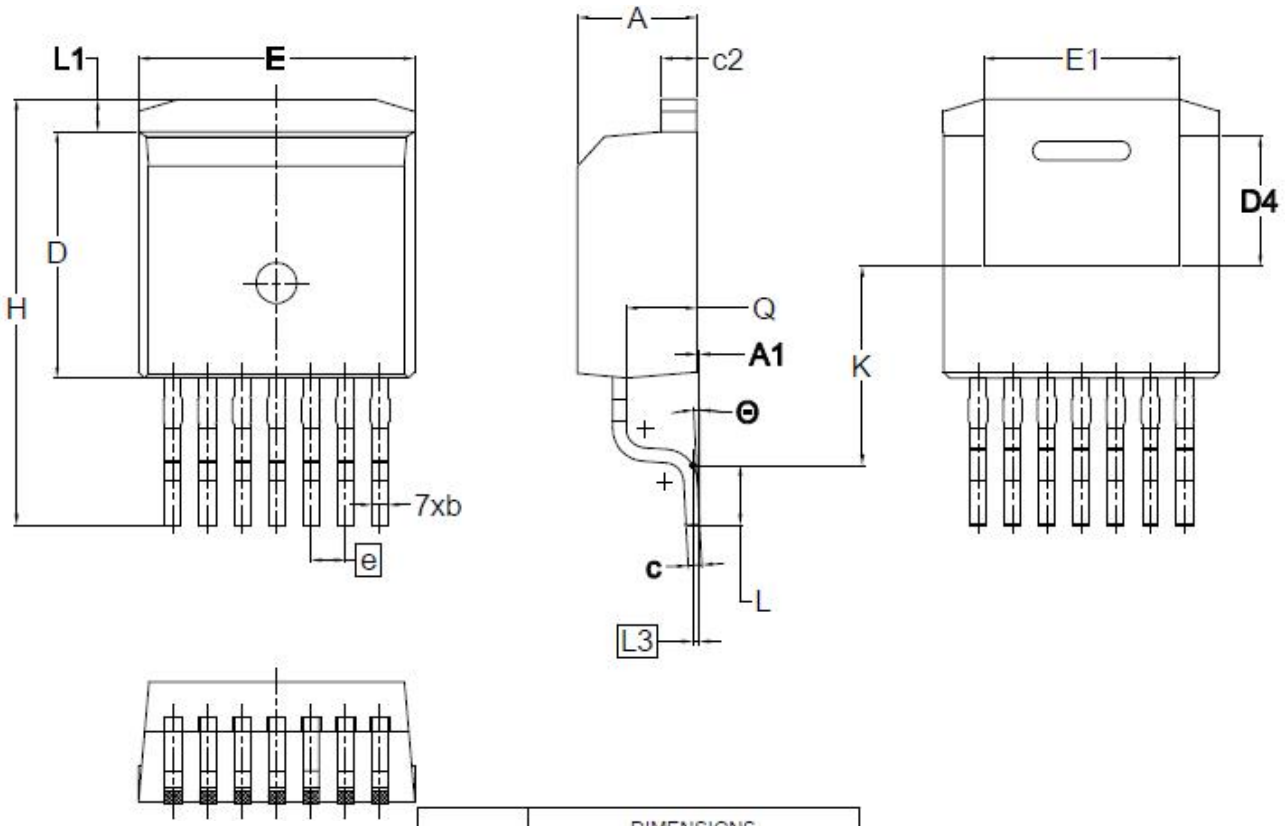


Figure 21. Switching Times vs. $R_{G(ext)}$

Package Dimensions

Package TO-263-7L



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.30	4.40	4.50
A1	0.00	0.10	0.25
b	0.50	0.60	0.70
c	0.45	0.50	0.60
c2	1.20	1.30	1.40
D	8.93	9.08	9.23
D4	4.65	4.80	4.95
E	10.08	10.18	10.28
E1	6.82	7.22	7.62
e	1.27 BSC		
H	15.00	15.70	16.00
K	7.30		
L	1.90	2.20	2.50
L1	1.00	1.20	1.40
L3	0.25 BSC		
Q	2.45	2.60	2.75
Θ	0°	3°	7°

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